| TRANSMITTAL LETTER (General - Patent Pending) | Docket No. 51889/2 |
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In Re Application Of: **D uglas R. Hackler, Sr. et al.**

| Serial No. | Filing Date | Examiner | Group Art Unit |
|---|---|---|---|
| 10/613,169 | July 3, 2003 | Not yet ssigned | 2811 |

Title: **MULTI-CONFIGURABLE INDEPENDENTLY MULTI-GATED MOSFET**

TO THE COMMISSIONER FOR PATENTS:

Transmitted herewith is:

**Inf rmation Disclosure Statement**
**PTO-1449 with copies of cited references**
**Postcard**

in the above identified application.

- ☒ No additional fee is required.
- ☐ A check in the amount of is attached.
- ☐ The Director is hereby authorized to charge and credit Deposit Account No. as described below.
  - ☐ Charge the amount of
  - ☐ Credit any overpayment.
  - ☐ Charge any additional fee required.

*Signature*

Dated: October 31, 2003

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I certify that this document and fee is being deposited on Oct. 31, 2003 with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

*Signature of Person Mailing Correspondence*

**John R. Thompson**

*Typed or Printed Name of Person Mailing Correspondence*

cc:

PATENT APPLICATION
Docket No.: 51889/2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

| | | |
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| In re application of: | | |
| | Douglas R. Hackler, Sr. et al. | Art Unit |
| Serial No.: | 10/613,169 | 2811 |
| Filed: | July 3, 2003 | |
| For: | MULTI-CONFIGURABLE INDEPENDENTLY MULTI-GATED MOSFET | |

INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R § 1.97

TO THE COMMISSIONER FOR PATENTS:

Pursuant to his (her) (their) duty of disclosure, applicant(s) enclose(s) copies (a copy) of the document(s) listed on the accompanying Form PTO-1449.

1. This information disclosure statement is being submitted:

a. ☒ Within three months of the filing date of the above-identified application or within three months of the date of entry of the national stage, or before the mailing date of the first Office action on the merits, whichever event occurs last. (No statement under 37 CFR 1.97(e) is required.)

b. ☐ After the period set forth in paragraph 1a, but before the mailing date of either a final action or a notice of allowance. (Check box i. or ii.)

i. ☐ A $180.00 information disclosure statement submission fee set forth in 37 CFR 1.17(p) is enclosed.

ii. ☐ A statement specified by 37 CFR 1.97(e) is set forth below.

c. ☐ After the mailing date of a final action or notice of allowance and on or before payment of an issue fee. A statement specified by 37 CFR 1.97(e) is set forth below. A petition requesting consideration of the information disclosure statement and the $130.00 petition fee set forth in 37 CFR 1.17(i) are enclosed.

d. ☐ Concurrent with the filing of a Request for Continued Examination

2. ☐ The attorney or agent signing below hereby states that:

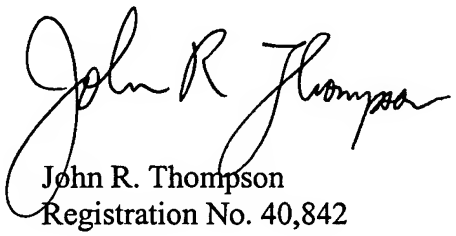
a. ☐ each item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

b. ☐ no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the statement after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the information disclosure statement.

3. ☐ Applicant(s) set forth below concise explanations of the relevance of each document not in the English language and/or selected document(s) in the English language.

DATED this 31 day of October, 2003.

Respectfully submitted,



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Sheet 1 of 7

| FORM PTO-1449 (REV. 7-80) | U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | ATTY. DOCKET NO. 51889/2 US | APPLICATION NO. 10/613,169 |
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| Title: **MULTI-CONFIGURABLE INDEPENDENTLY MULTI-GATED MOSFET** | | FILING DATE- July 3, 2003 | |



U.S. PATENT DOCUMENTS

| EXAMINER INITIAL | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
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